Shenzhen Tuofeng Semiconductor Technology Co., Ltd

P -CHANNEL ENHANCEMENT MODE POWER MOSFET

TF070P03N

● General Description

The TF070P03N combines advanced trench MOSFETtechnology with a low resistance package to provide extremely low $R_{DS(ON)}$.

● Features

Advance high cell density Trench technology

Low $R_{DS(ON)}$ to minimize conductive loss

Low Gate Charge for fast switching

Low Thermal resistance

●Application

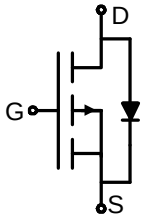
MB/VGA Vcore

SMPS 2nd Synchronous Rectifier

POL application

BLDC Motor driver

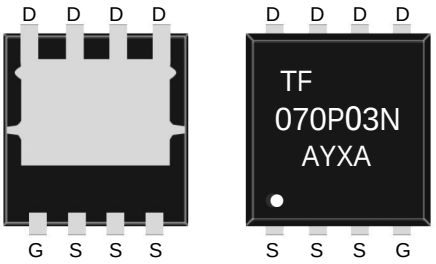
● Product Summary



V_{DS} =-30V I_D=-70A

$R_{DSON(-10V\ typ)}$ =7.5mΩ

$R_{DSON(-4.5V\ typ)}$ =11mΩ



PDFNWB5x6-8L

●Ordering Information:

Part NO.	TF070P03N
Marking1	070P03N
Marking2	TF:tuofeng; Y:year code; X:Week; AA:device code;
Basic ordering unit (pcs)	5000

●Absolute Maximum Ratings (T_C =25℃)

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@}T_C$=25℃	-70	A
	$I_{D@}T_C$=75℃	-49	A
	$I_{D\ @}T_C$=100℃	-42	A
Pulsed Drain Current ①	I_{DM}	-230	A
Total Power Dissipation②	$P_D@T_C$=25℃	60	W
Total Power Dissipation	$P_D@T_A$=25℃	2.0	W
Operating Junction Temperature	T_J	-55 to 150	℃
Storage Temperature	T_{STG}	-55 to 150	℃

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case②	R_{thJC}	-	-	3.5	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	50	° C/W
Soldering temperature, wavesoldering for 8s	T_{sold}	-	-	265	° C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =-250uA	-30			V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} =V_{DS}, I_D =-250uA	-1.0	-1.5	-2.0	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-28V, V_{GS} =0V			-1.0	uA
Gate- Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS} =0V			±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-20A		7.5	9.0	mΩ
		V_{GS}=-4.5V, I_D=-15A		11	14	mΩ
Forward Transconductance	g_{FS}	V_{DS} =-10V, I_D=-10A		12		S
Source-drain voltage	V_{SD}	Is=-20A		0.85	1.00	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz V_{DD} = -30V V_{GS} = 0V	-	2497	-	pF
Output capacitance	C_{oss}		-	240	-	
Reverse transfer capacitance	C_{rss}		-	230	-	

●Gate Charge characteristics(T_a = 25℃)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	V_{DD} = -15V I_D = -20A V_{GS} = -10V	-	32.0	-	nC
Gate - Source charge	Q_{gs}		-	6.60	-	
Gate - Drain charge	Q_{gd}		-	8.00	-	
Turn-On Delay Time Time	$t_{d(on)}$	V_{GS} = -10V V_{DD} =-15V R_L = 3.0Ω I_D =-30A	-	14.0	-	nS
Turn-On Rise Time	t_r		-	20.0	-	
Turn-Off Delay Time	$t_{d(off)}$		-	56.0	-	
Turn-Off Fall Time	t_f		-	48.0	-	

Note:
① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;
② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

P- Channel Typical Characteristics

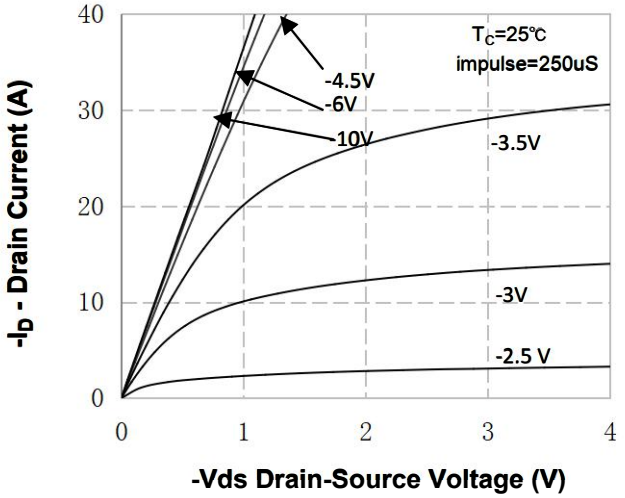


Figure 1. On-Region Characteristics

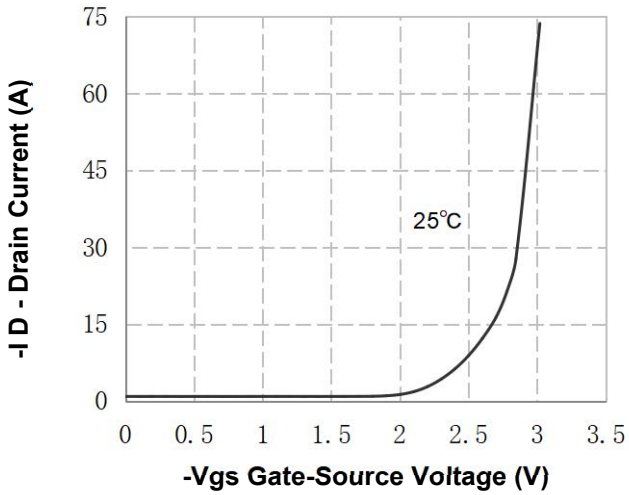


Figure 2. Transfer Characteristics

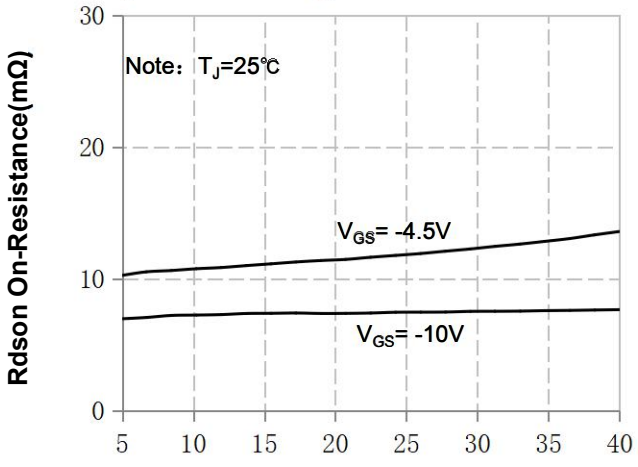


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

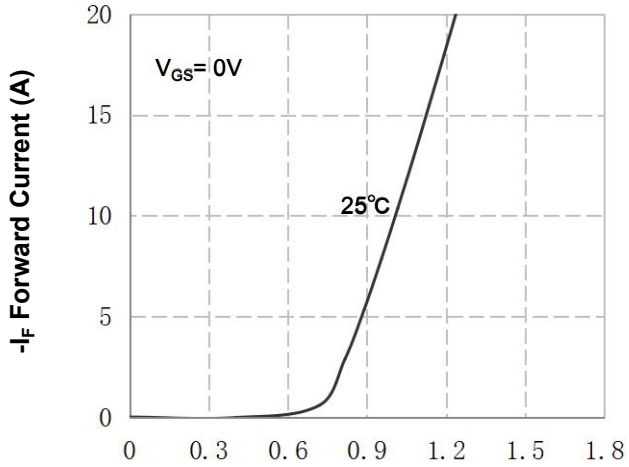


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

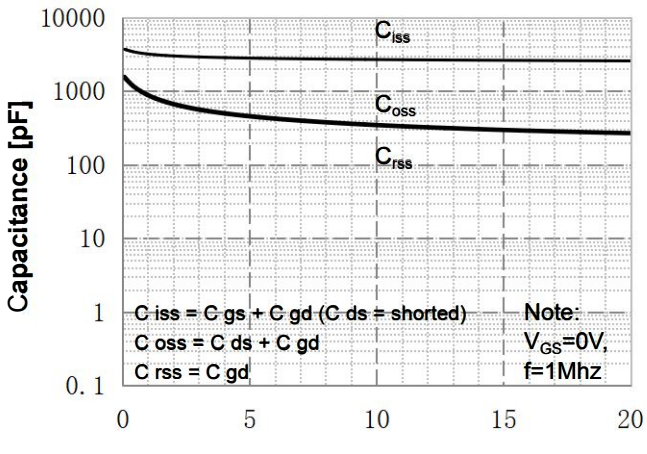


Figure 5. Capacitance Characteristics

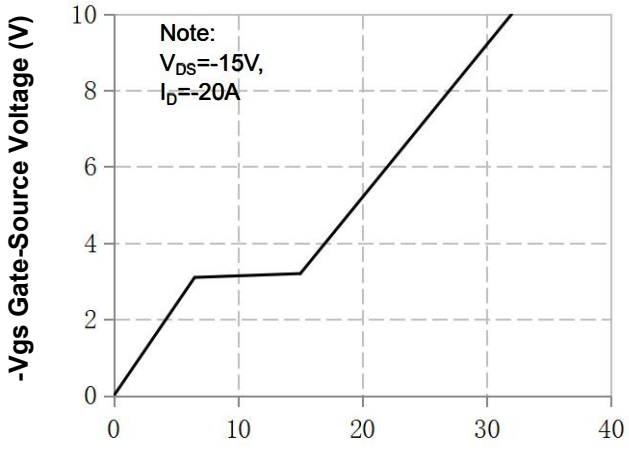


Figure 6. Gate Charge Characteristics

P- Channel Typical Characteristics (Continued)

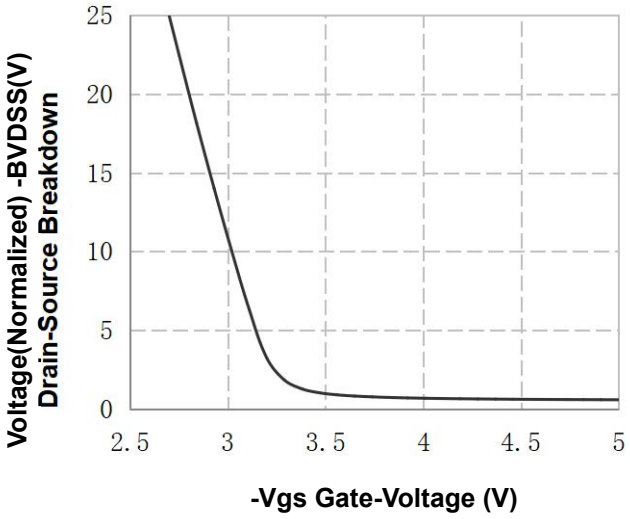


Figure 7. Breakdown Voltage Variation vs Gate-Voltage

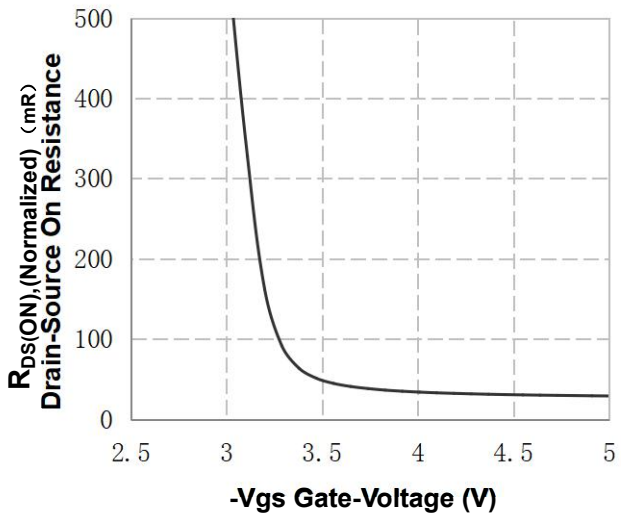


Figure 8. On-Resistance Variation vs Gate Voltage

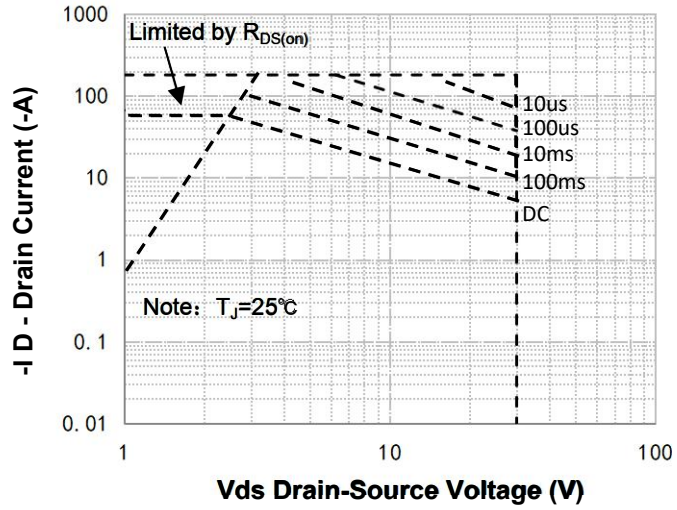


Figure 9. Maximum Safe Operating Area

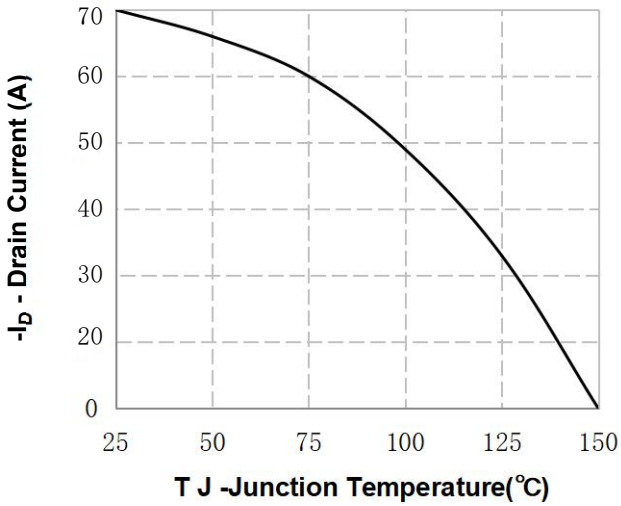


Figure 10. Maximum PContinuous Drain Currentvs Case Temperature

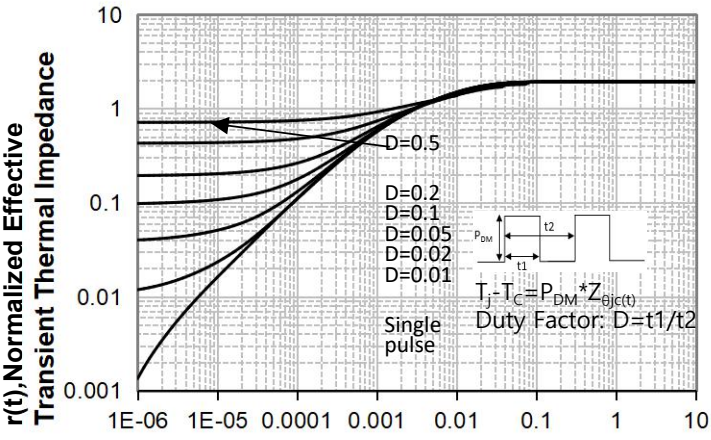
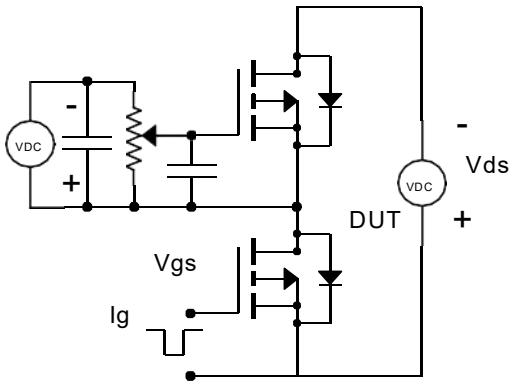
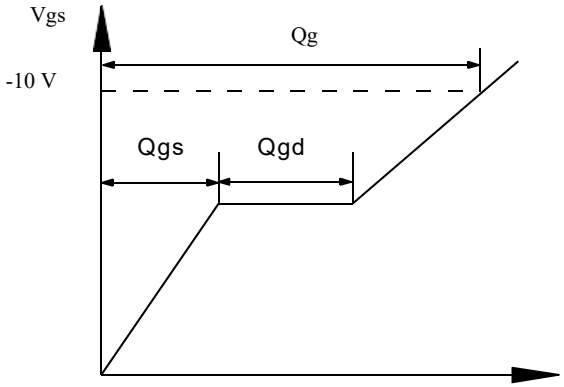


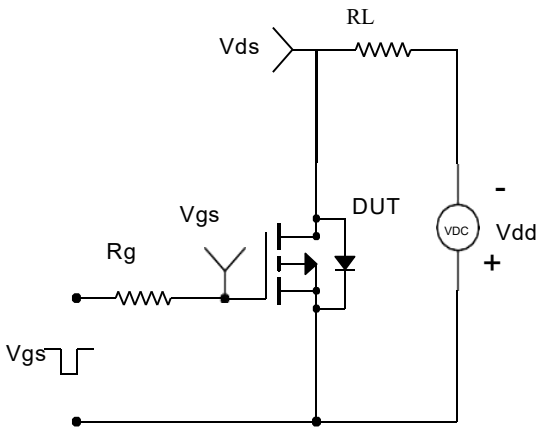
Figure 11. Transient Thermal Response Curve

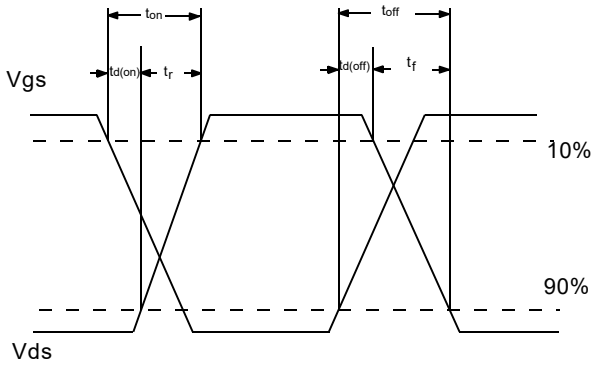
Gate Charge Test Circuit & Waveform



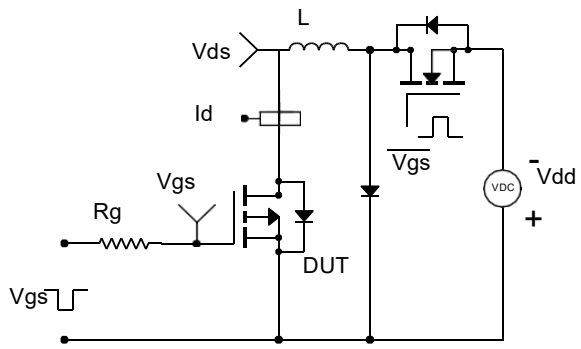


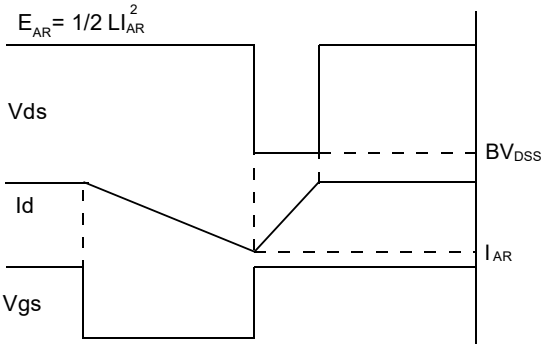
Resistive Switching Test Circuit & Waveforms



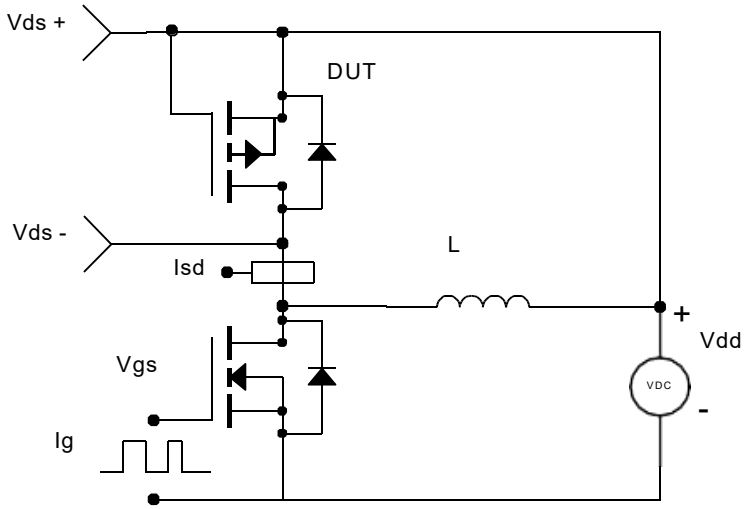


Unclamped Inductive Switching Test Circuit & Waveforms

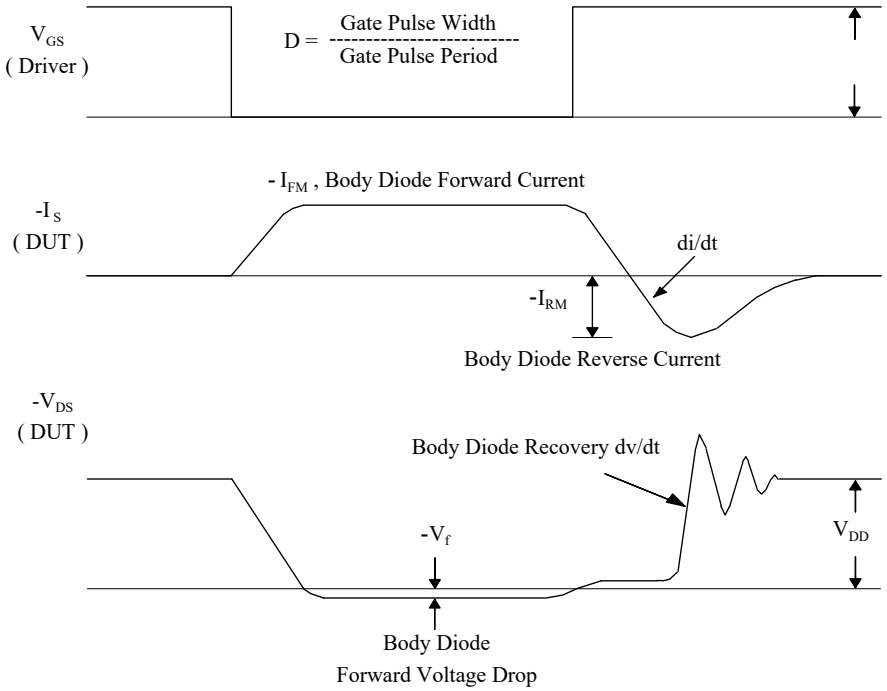




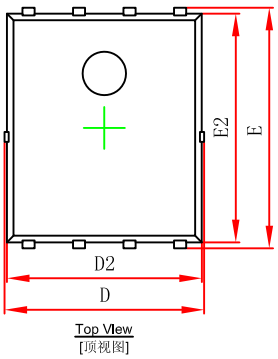
Peak Diode Recovery dv/dt Test Circuit & Waveforms

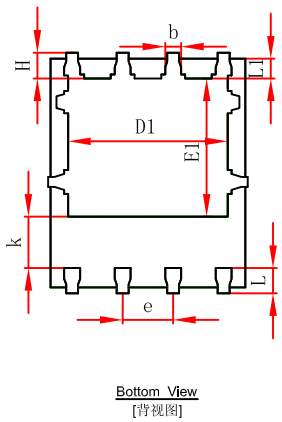


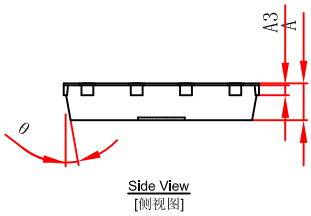
• dv/dt controlled by R_G
• I_{SD} controlled by pulse period



PDFNWB5x6-8L Package Outline Dimensions

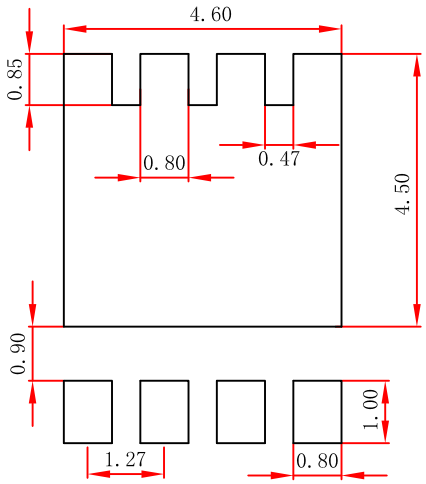






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.